

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



are patent application of

Hiroyuki Kunishima, et al.

Serial No.: 10/613,069

Group Art Unit: Not Yet Assigned

Filing Date: July 7, 2003

Examiner: Unknown

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD  
THEREOF

Honorable Commissioner of Patent  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following document listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copy of the listed document is provided herewith for the convenience of the Examiner.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,

Sean M. McGinn

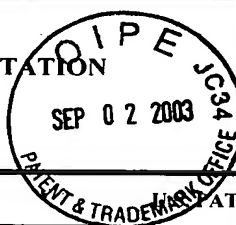
Registration No. 34,386

Date: 9/02/03

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# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional) <b>NE-70085US</b>	Application Number <b>10/613,069</b>
Applicant(s) <b>Hiroyuki KUNISHIMA, et al.</b>	
Filing Date <b>July 7, 2003</b>	Group Art Unit <b>Not Yet Assigned</b>

## PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		T. Takewaki, et al., "Formation of grain-grain copper interconnects by a low-energy ion bombardment process for high-speed ULSIs", <u>Materials Chemistry and Physics</u> 41 (1995) pp. 182-191.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.